CORRECTION

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Correction: Plasma enhanced atomic layer deposition of Ga₂O₃ thin films

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Correction for 'Plasma enhanced atomic layer deposition of Ga₂O₃ thin films' by Ranjith K. Ramachandran *et al.*, *J. Mater. Chem. A*, 2014, 2, 19232–19238.

On the y-axis of Fig. 4, the authors mistyped the unit of thickness as "Å" instead of "nm". This has now been corrected in the new Fig. 4 provided, as shown.

Fig. 4 Thickness of the Ga₂O₃ films deposited at 200 °C on SiO₂/Si substrates against the number of ALD cycles.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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